

1.4 Quick reference data

Table 1. Quick reference data

$4.75\text{ V} \leq V_{\text{SUP}} \leq 5.25\text{ V}$; $-40\text{ }^{\circ}\text{C} \leq T_{\text{amb}} \leq +85\text{ }^{\circ}\text{C}$; maximum current; input and output is terminated with $50\text{ }\Omega$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{SUP}	supply voltage		[1] 4.75	5.0	5.25	V
$I_{\text{CC(tot)}}$	total supply current	maximum current	160	195	230	mA
		optimized current	[2] -	185	-	mA
		minimum current	-	120	-	mA
		power-down current	-	15	-	mA
T_{amb}	ambient temperature		-40	+25	+85	$^{\circ}\text{C}$
G_{p}	power gain	minimum attenuation				
		$700\text{ MHz} \leq f \leq 1400\text{ MHz}$	26	30	33	dB
		$1400\text{ MHz} \leq f \leq 1700\text{ MHz}$	26	29.5	33	dB
		$1700\text{ MHz} \leq f \leq 2200\text{ MHz}$	26	29	33	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	25	28	31	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	22	26	30	dB
α_{range}	attenuation range	$700\text{ MHz} \leq f \leq 2200\text{ MHz}$	28	31.5	35	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	27	30.5	34	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	26	29.5	33	dB
NF	noise figure	minimum attenuation				
		$700\text{ MHz} \leq f \leq 2200\text{ MHz}$	-	6.5	8.5	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	-	7	9	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	-	8	10	dB
		maximum attenuation				
		$700\text{ MHz} \leq f \leq 2200\text{ MHz}$	-	27.5	30.5	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	-	28	31	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	-	28.5	32	dB
IP3O	output third-order intercept point	minimum attenuation	[3]			
		$700\text{ MHz} \leq f \leq 1400\text{ MHz}$	34	39	-	dBm
		$1400\text{ MHz} \leq f \leq 1700\text{ MHz}$	32	37	-	dBm
		$1700\text{ MHz} \leq f \leq 2200\text{ MHz}$	30	35	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	28	34	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$; $C_{\text{sh}} = 0.68\text{ pF}$	[4] 30	35	-	dBm
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	24	30	-	dBm
		maximum attenuation	[3]			
		$700\text{ MHz} \leq f \leq 1400\text{ MHz}$	-	35	-	dBm
		$1400\text{ MHz} \leq f \leq 1700\text{ MHz}$	-	33	-	dBm
		$1700\text{ MHz} \leq f \leq 2200\text{ MHz}$	-	31	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	-	30	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$; $C_{\text{sh}} = 0.68\text{ pF}$	[4] -	30	-	dBm
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	-	25	-	dBm

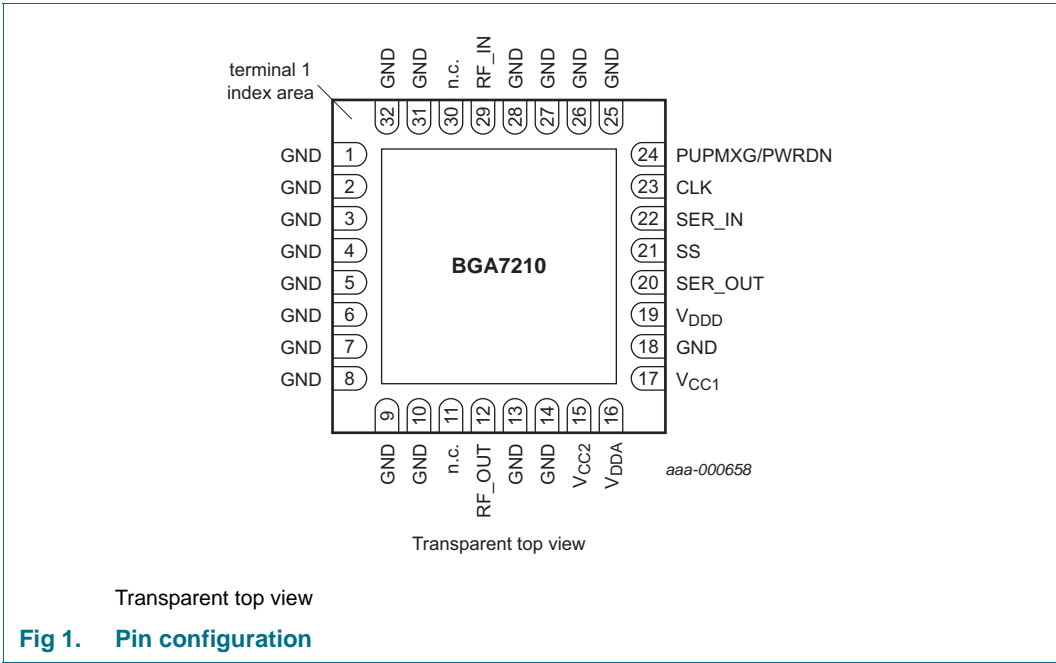
Table 1. Quick reference data ...continued
4.75 V ≤ V_{SUP} ≤ 5.25 V; −40 °C ≤ T_{amb} ≤ +85 °C; maximum current; input and output is terminated with 50 Ω; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
P _{L(1dB)}	output power at 1 dB gain compression	minimum attenuation				
		700 MHz ≤ f ≤ 2800 MHz	18	21	-	dBm
		2200 MHz ≤ f ≤ 2800 MHz; C _{sh} = 0.68 pF [4]	20	23	-	dBm
		3400 MHz ≤ f ≤ 3800 MHz	16	19	-	dBm

- [1] Supply voltage on pins RF_OUT, V_{CC2}, V_{DDA}, V_{CC1} and V_{DD}.
[2] See [Section 9.2](#).
[3] P_i = −23 dBm per tone; Δf = 10 MHz.
[4] See [Section 11](#).

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
GND	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 13, 14, 18, 25, 26, 27, 28, 31, 32	Ground
n.c.	11, 30	not connected
RF_OUT	12	RF output and supply to amplifier 2
V _{CC2}	15	Supply voltage to amplifier 2
V _{DDA}	16	Analog supply voltage to DSA

Table 2. Pin description ...continued

Symbol	Pin	Description
V _{CC1}	17	Supply voltage to amplifier 1
V _{DD}	19	Digital supply voltage to digital controller
SER_OUT	20	SPI data output
SS	21	SPI slave select (0 = select; 1 = deselect)
SER_IN	22	SPI data input
CLK	23	SPI clock input
PUPMXG/PWRDN	24	Power-up gain attenuation / power down
RF_IN	29	RF input

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BGA7210	HVQFN32	plastic thermal enhanced very thin quad flat package; no leads; 32 terminals; body 5 × 5 × 0.85 mm	SOT617-3

4. Marking

Table 4. Marking

Type number	Marking code
BGA7210	7210

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{SUP}	supply voltage		[1] -0.6	+8	V
V _I	input voltage		[2] -0.6	+8	V
V _O	output voltage		[3] -0.6	+8	V
I _I	input current		[4] -20	+20	mA
I _O	output current		[5] -20	+20	mA
P _{RFIN}	power on pin RF_IN		-	30	dBm
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According to JEDEC standard 22-A114E	-	4	kV
		Charged Device Model (CDM); According to JEDEC standard 22-C101B	-	2	kV

[1] Absolute maximum DC voltage on pins RF_OUT, V_{CC2}, V_{DDA}, V_{CC1}, V_{DD} and RF_IN.

[2] Absolute maximum DC voltage on pins SS, SER_IN, CLK and PUPMXG/PWRDN.

- [3] Absolute maximum DC voltage on pin SER_OUT.
 [4] Absolute maximum DC current through pins SS, SER_IN, CLK and PUPMXG/PWRDN.
 [5] Absolute maximum DC current through pin SER_OUT.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	$T_{sp} \leq 85\text{ °C}$	[1] 16	K/W

[1] T_{sp} is the temperature at the solder point.

7. Static characteristics

Table 7. Static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{SUP}	supply voltage		[1] 4.75	5.0	5.25	V
$I_{CC(tot)}$	total supply current	maximum	160	195	230	mA
		optimized current	[2] -	185	-	mA
		minimum current	-	120	-	mA
		power-down current	-	15	-	mA
T_{amb}	ambient temperature		-40	+25	+85	°C
I_{CC}	supply current	on pin RF_OUT	-	85	-	mA
	supply current	on pin V_{CC2}	-	45	-	mA
	supply current	on pin V_{DDA}	-	5	-	mA
	supply current	on pin V_{CC1}	-	55	-	mA
	supply current	on pin V_{DDD}	-	5	-	mA
V_{IL}	LOW-level input voltage		[3] -0.1	0	+0.8	V
V_{IH}	HIGH-level input voltage		[3] 2	3.3	$V_{SUP} + 0.1$	V
V_{OL}	LOW-level output voltage		[4] -0.1	0	+0.8	V
V_{OH}	HIGH-level output voltage		[4] 2.5	3.3	3.4	V
I_{OL}	LOW-level output current		[4] -15	-	0	mA
I_{OH}	HIGH-level output current		[4] 0	-	15	mA

[1] Supply voltage on pins RF_OUT, V_{CC2} , V_{DDA} , V_{CC1} and V_{DDD} .

[2] See [Section 9.2](#).

[3] Digital input pins are: SS, SER_IN, CLK and PUPMXG/PWRDN.

[4] Digital output pin is: SER_OUT.

8. Dynamic characteristics

Table 8. Dynamic characteristics

$4.75\text{ V} \leq V_{\text{SUP}} \leq 5.25\text{ V}$; $-40\text{ }^{\circ}\text{C} \leq T_{\text{amb}} \leq +85\text{ }^{\circ}\text{C}$; maximum current; input and output terminated with $50\text{ }\Omega$, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	minimum attenuation				
		$700\text{ MHz} \leq f \leq 1400\text{ MHz}$	26	30	33	dB
		$1400\text{ MHz} \leq f \leq 1700\text{ MHz}$	26	29.5	33	dB
		$1700\text{ MHz} \leq f \leq 2200\text{ MHz}$	26	29	33	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	25	28	31	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	22	26	30	dB
$\Delta G/\Delta T$	gain variation with temperature		-0.03	-0.006	0	dB/ $^{\circ}\text{C}$
$\Delta G/\Delta V_{\text{SUP}}$	gain variation with supply voltage		-0.2	-	+0.2	dB/V
α_{range}	attenuation range	$700\text{ MHz} \leq f \leq 2200\text{ MHz}$	28	31.5	35	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	27	30.5	34	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	26	29.5	33	dB
α_{step}	attenuation step	$700\text{ MHz} \leq f \leq 2800\text{ MHz}$	0	0.5	1	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	0	0.5	1.2	dB
ΔG_p	power gain variation	$700\text{ MHz} \leq f \leq 3800\text{ MHz}$	[1] -1.5	-	+1.5	dB
		$700\text{ MHz} \leq f \leq 2200\text{ MHz}$	[2] $-(0.5 + 0.025 \times i_{\alpha})$	-	$+(0.5 + 0.025 \times i_{\alpha})$	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	[2] $-(0.3 + 0.025 \times i_{\alpha})$	-	$+(0.3 + 0.025 \times i_{\alpha})$	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	[2] $-(0.5 + 0.025 \times i_{\alpha})$	-	$+(0.5 + 0.025 \times i_{\alpha})$	dB
$G_{p(\text{flat})}$	power gain flatness	$700\text{ MHz} \leq f \leq 3800\text{ MHz}$; per 200 MHz	-	-	1	dB
RL_{in}	input return loss	$700\text{ MHz} \leq f \leq 3800\text{ MHz}$	10	-	-	dB
RL_{out}	output return loss	$700\text{ MHz} \leq f \leq 3800\text{ MHz}$	7	-	-	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$; $C_{\text{sh}} = 0.68\text{ pF}$	10	-	-	dB
NF	noise figure	minimum attenuation				
		$700\text{ MHz} \leq f \leq 2200\text{ MHz}$	-	6.5	8.5	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	-	7	9	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	-	8	10	dB
		maximum attenuation				
		$700\text{ MHz} \leq f \leq 2200\text{ MHz}$	-	27.5	30.5	dB
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	-	28	31	dB
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	-	28.5	32	dB

Table 8. Dynamic characteristics ...continued

$4.75\text{ V} \leq V_{SUP} \leq 5.25\text{ V}$; $-40\text{ }^{\circ}\text{C} \leq T_{amb} \leq +85\text{ }^{\circ}\text{C}$; maximum current; input and output terminated with $50\text{ }\Omega$, unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
IP _{3O}	output third-order intercept point	minimum attenuation [3]				
		$700\text{ MHz} \leq f \leq 1400\text{ MHz}$	34	39	-	dBm
		$1400\text{ MHz} \leq f \leq 1700\text{ MHz}$	32	37	-	dBm
		$1700\text{ MHz} \leq f \leq 2200\text{ MHz}$	30	35	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	28	33	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$; $C_{sh} = 0.68\text{ pF}$ [4]	30	35	-	dBm
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	24	27	-	dBm
		maximum attenuation [3]				
		$700\text{ MHz} \leq f \leq 1400\text{ MHz}$	-	35	-	dBm
		$1400\text{ MHz} \leq f \leq 1700\text{ MHz}$	-	33	-	dBm
		$1700\text{ MHz} \leq f \leq 2200\text{ MHz}$	-	31	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$	-	30	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$; $C_{sh} = 0.68\text{ pF}$ [4]	-	30	-	dBm
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	-	25	-	dBm
P _{L(1dB)}	output power at 1 dB gain compression	minimum attenuation				
		$700\text{ MHz} \leq f \leq 2800\text{ MHz}$	18	21	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$; $C_{sh} = 0.68\text{ pF}$ [4]	20	23	-	dBm
		$3400\text{ MHz} \leq f \leq 3800\text{ MHz}$	16	19	-	dBm
		maximum attenuation				
		$700\text{ MHz} \leq f \leq 2800\text{ MHz}$	-	20	-	dBm
		$2200\text{ MHz} \leq f \leq 2800\text{ MHz}$; $C_{sh} = 0.68\text{ pF}$ [4]	-	20	-	dBm
t _{d(pd)}	power-down delay time	[5]	-	100	-	ns
		[5]	-	5	-	μs
		[5]	-	100	-	ns
t _{d(pu)}	power-up delay time	[5]	-	5	-	μs
t _{resp(α)}	attenuation response time	[5] [6]	-	100	-	ns

[1] Normalized to maximum gain and attenuation.

[2] i_{α} specifies the decimal attenuation step, ranging from 0 to 63.

[3] $P_i = -23\text{ dBm}$ per tone; $\Delta f = 10\text{ MHz}$.

[4] See [Section 11](#).

[5] To within 0.1 dB of final gain state.

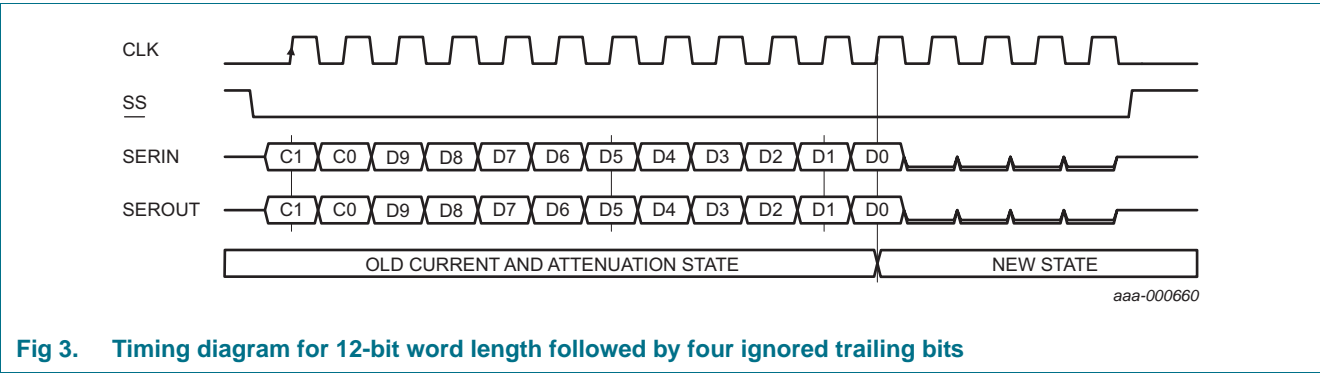
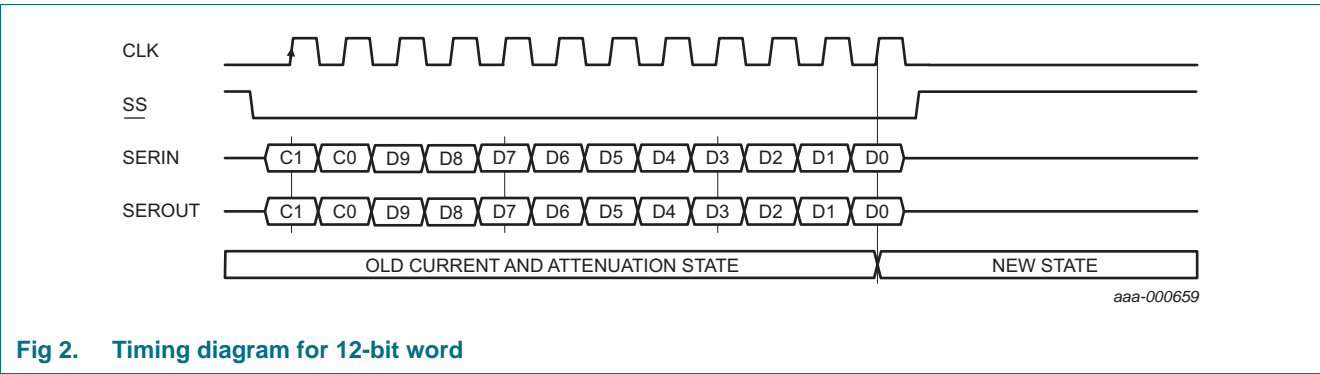
[6] After last SPI bit is clocked in.

9. Serial Peripheral Interface

9.1 Command word format

The Serial Peripheral Interface (SPI) operates in mode 0. This means that when the SPI is inactive the clock pin is logically LOW. When the SPI interface is active the data is clocked in at the rising edge of the clock pulse; data is clocked out at the negative edge. The

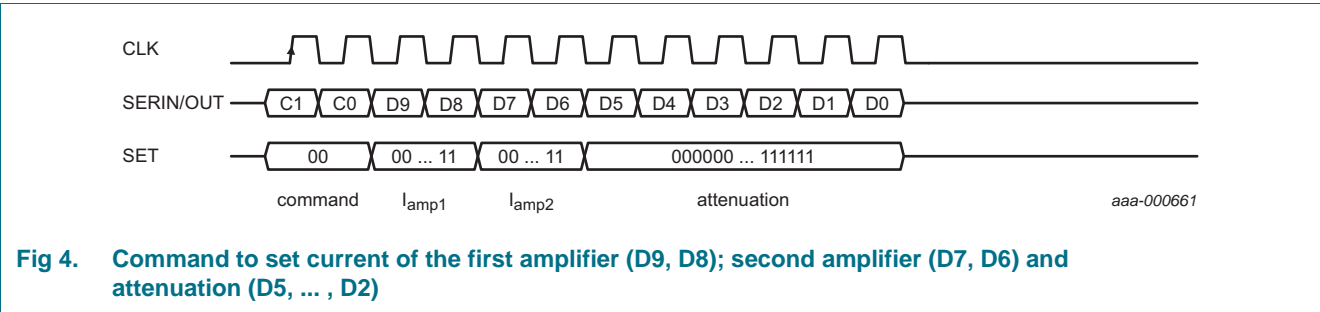
control word length is 12 bits (see [Figure 2](#)), however the word length can be extended appropriately with trailing zeros (see [Figure 3](#)).



The word written on the input (SER_IN) will be replicated on the output (SER_OUT)

9.2 Setting current and attenuation

The current and attenuation are set by bits D9 to D0 and are preceded by the command bits C0 and C1, which are always set to logic LOW, see [Figure 4](#). If all bits are set to logic LOW (0x000) then current is at maximum and attenuation is at minimum; if all bits are set to logic HIGH (0x3FF) then current is at minimum and attenuation is at maximum.



Depending on the attenuation setting the current through the first amplifier and the second amplifier can be optimized, without compromising on linearity. At attenuations less than 9 dB the current in the first amplifier can be reduced with 10 mA; at attenuations equal or larger than 9 dB the current in the second amplifier can be reduced by 15 mA.

Table 9. Current first amplifier truth table

D9, D8	Current reduction (mA)
0x0	0
0x1	-10
0x2	-20
0x3	-30

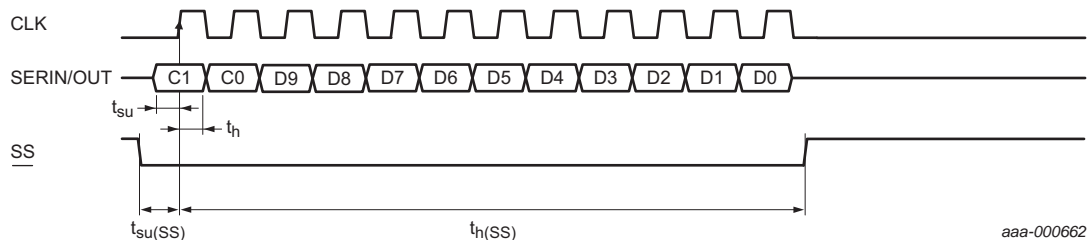
Table 10. Current second amplifier truth table

D7, D6	Current reduction (mA)
0x0	0
0x1	-15
0x2	-30
0x3	-45

Table 11. Attenuation truth table; major states only

D5, D4, D3, D2, D1, D0	Attenuation (dB)
0x00	0
0x01	0.5
0x02	1
0x04	2
0x08	4
0x10	8
0x20	16
0x3F	31.5

9.3 SPI timing

**Fig 5. Timing diagram****Table 12. SPI timing**

$4.75\text{ V} \leq V_{SUP} \leq 5.25\text{ V}$; $-40\text{ }^{\circ}\text{C} \leq T_{amb} \leq +85\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SPI}	SPI frequency		0.1	-	20	MHz
t_{su}	set-up time		10	-	-	ns
t_h	hold time		10	-	-	ns
$t_{su(SS)}$	set-up time on pin SS		10	-	-	ns
$t_{h(SS)}$	hold time on pin SS		$10 + 11 / f_{SPI}$	-	-	ns

10. Power-up and power save

The PUPMXG/PWRDN pin determines the attenuation and currents at start-up of the chip (see [Table 13](#)). After start-up it can be used to power-down the device.

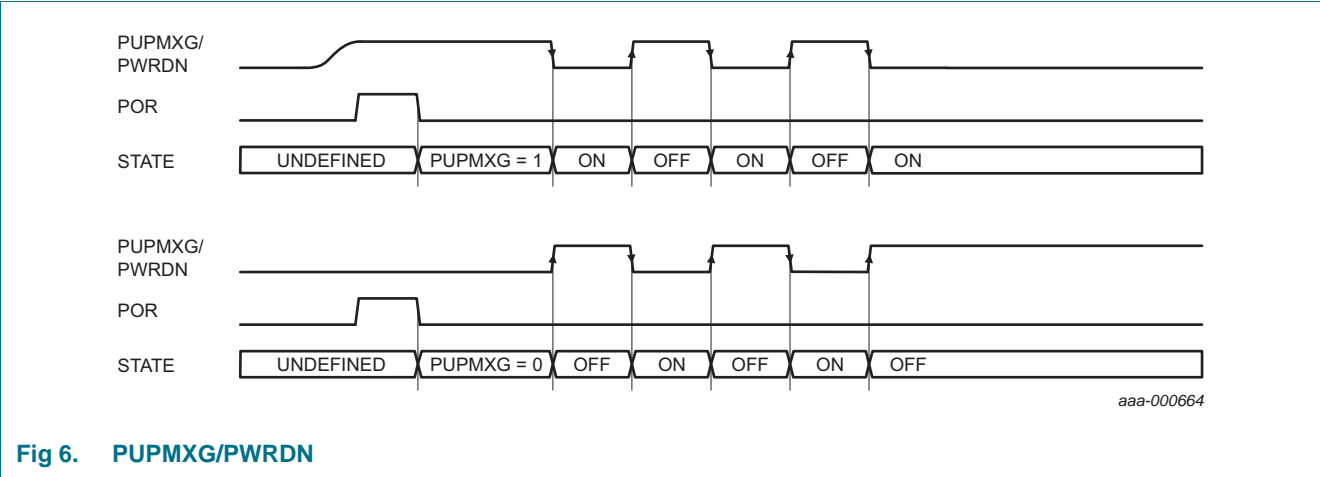


Fig 6. PUPMXG/PWRDN

Table 13. Power-up truth table

PUPMXG/PWRDN	Current (mA)	Attenuation (dB)
0	120	31.5
1	195	0

11. Application information

11.1 Application board

A customer application board is available from NXP upon request. It includes USB interface circuitry and customer software to facilitate evaluation of the BGA7210.

The final application shall be terminated with 50 Ω and decoupled as depicted in [Figure 7](#). The ground leads and exposed paddle should be connected directly to the ground plane. A sufficient number of via holes should be provided to connect the top and bottom ground planes in the final application board. Sufficient cooling should be provided that the temperature of the exposed die pad does not exceed 85 °C.

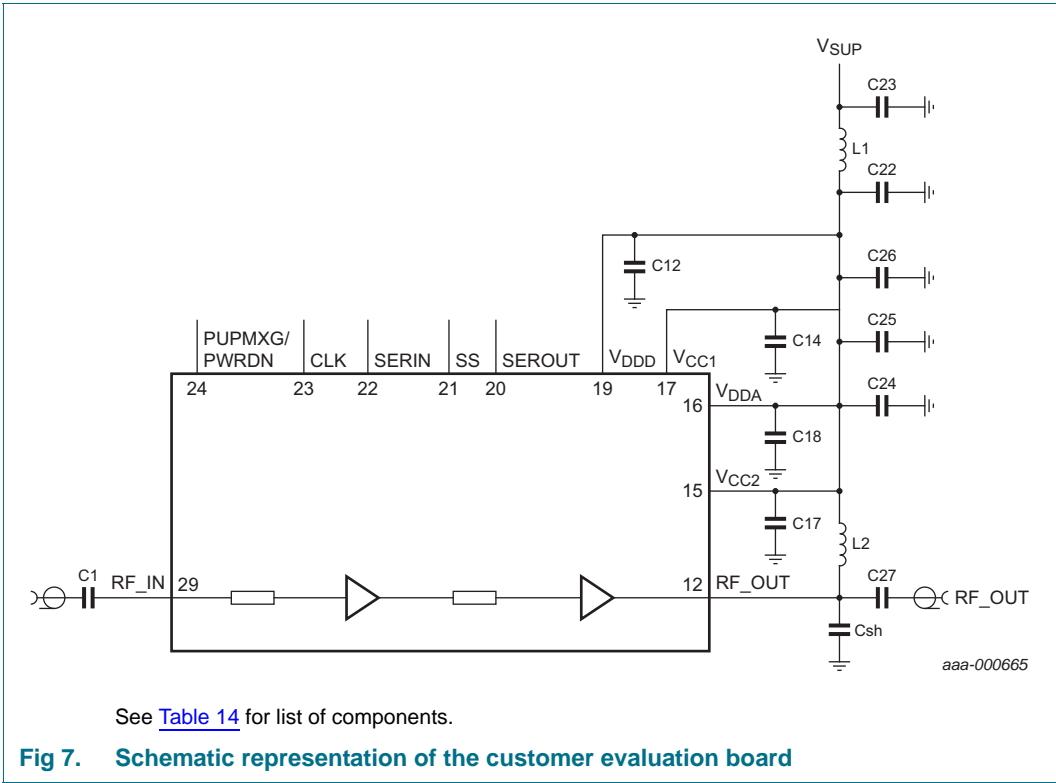
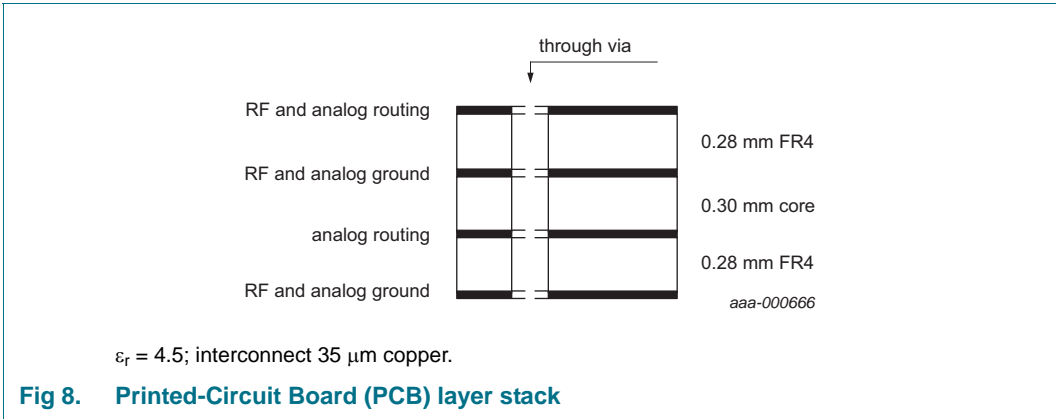


Table 14. List of components

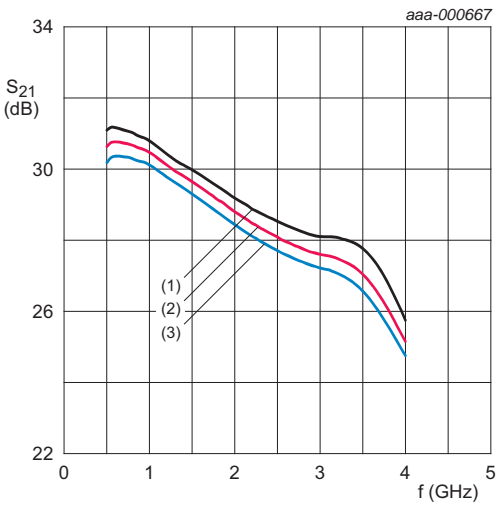
See [Figure 7](#) for schematics.

Component	Description	Value	Remarks
C1, C27	DC blocking capacitor	100 pF	Murata GRM
C12	decoupling capacitor	100 nF	close to pin 19
C14	decoupling capacitor	100 nF	close to pin 17
C17	decoupling capacitor	100 nF	close to pin 15
C18	decoupling capacitor	100 nF	close to pin 16
C22	optional decoupling capacitor	10 μ F	part of optional ripple filter
C23	optional decoupling capacitor	10 μ F	part of optional ripple filter
C24	decoupling capacitor	100 pF	
C25	decoupling capacitor	100 nF	
C26	decoupling capacitor	4.7 μ F	
C _{sh}	optional matching capacitor to improve linearity at 2.2 GHz to 2.8 GHz	0.68 pF	Murata GRM; shall be located 5.5 mm from pin RF-OUT when using FR4 PCB described below.
L1	optional inductor	820 nH	part of optional ripple filter
L2	inductor	22 nH	Murata LQW 18

The recommended FR4 PCB layer stack is described in [Figure 8](#). A 50 Ω coplanar grounded wave guide can be implemented by a 0.48 mm RF track and a clearance between the track and the ground planes of 1 mm on both sides.



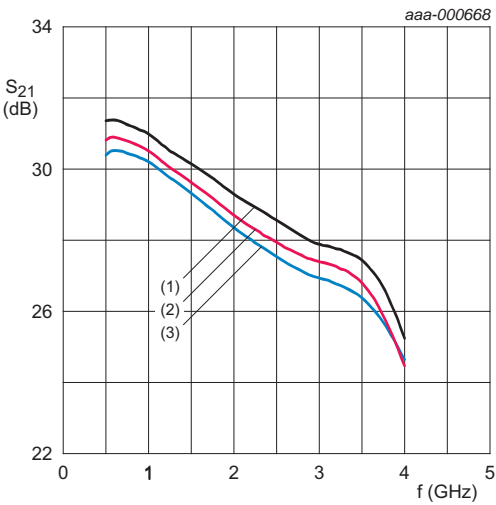
11.2 Characteristics



$V_{SUP} = 5\text{ V}$; maximum current setting.

- (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = +85\text{ }^{\circ}\text{C}$

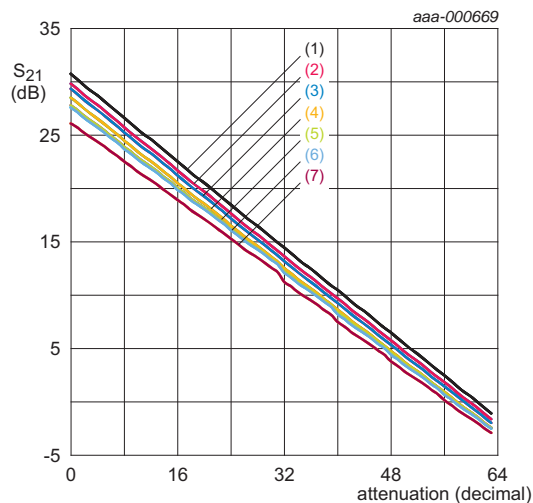
Fig 9. Maximum power gain as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; maximum current setting and shunt capacitor (C_{sh}).

- (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = +85\text{ }^{\circ}\text{C}$

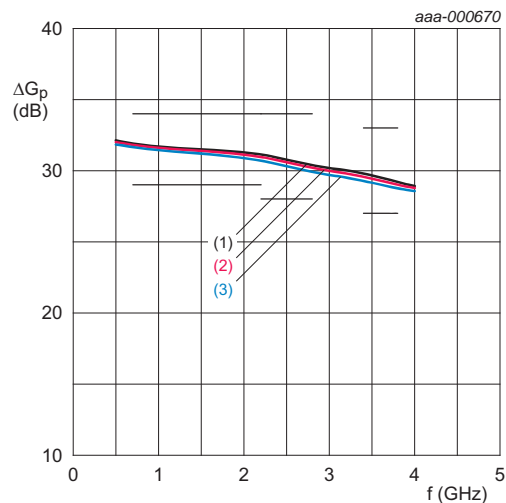
Fig 10. Maximum power gain with shunt capacitor as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; maximum current setting.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

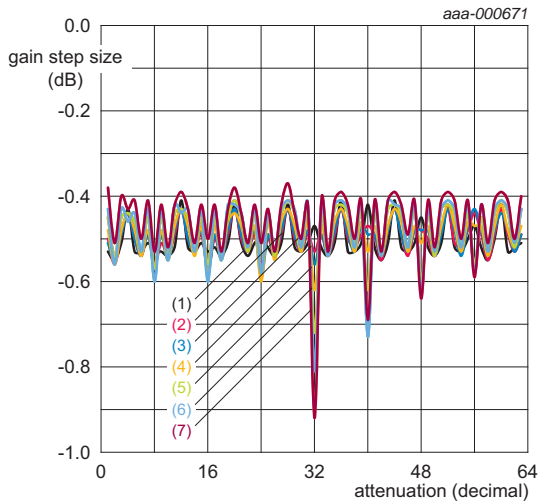
Fig 11. Power gain as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; maximum current setting.

- (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = +85\text{ }^{\circ}\text{C}$

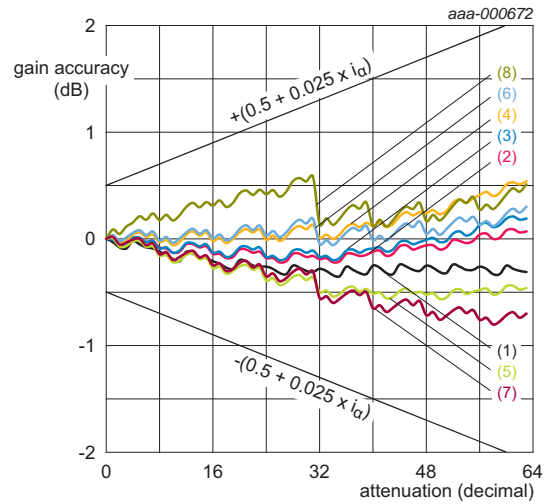
Fig 12. Power gain range as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; maximum current setting.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

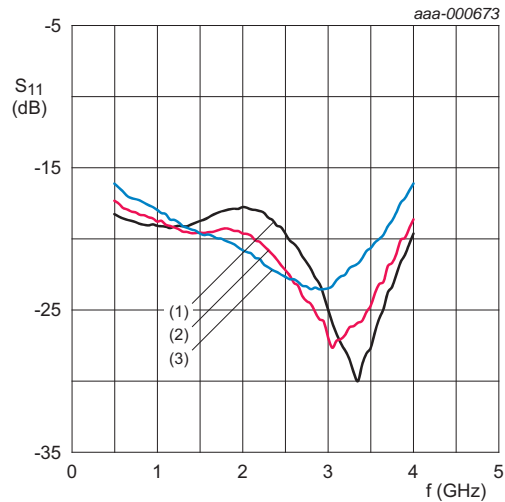
Fig 13. Gain step size as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; maximum current setting.

- (1) $f = 0.7\text{ GHz}$; $\alpha_{range} = 31.5\text{ dB}$
- (2) $f = 1.4\text{ GHz}$; $\alpha_{range} = 31.5\text{ dB}$
- (3) $f = 1.7\text{ GHz}$; $\alpha_{range} = 31.5\text{ dB}$
- (4) $f = 2.2\text{ GHz}$; $\alpha_{range} = 31.5\text{ dB}$
- (5) $f = 2.2\text{ GHz}$; $\alpha_{range} = 30.5\text{ dB}$
- (6) $f = 2.8\text{ GHz}$; $\alpha_{range} = 30.5\text{ dB}$
- (7) $f = 2.8\text{ GHz}$; $\alpha_{range} = 29.5\text{ dB}$
- (8) $f = 3.8\text{ GHz}$; $\alpha_{range} = 29.5\text{ dB}$

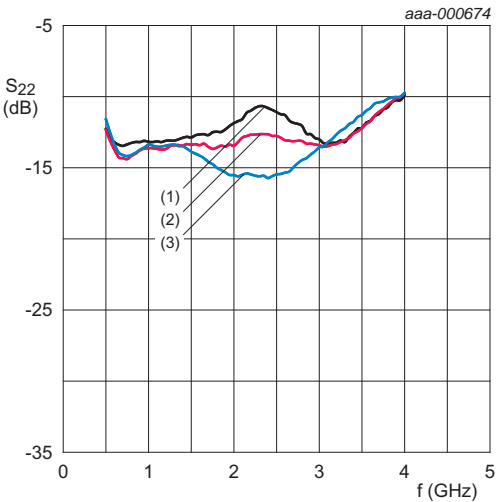
Fig 14. Power gain accuracy as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; maximum current setting;
minimum attenuation.

- (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = +85\text{ }^{\circ}\text{C}$

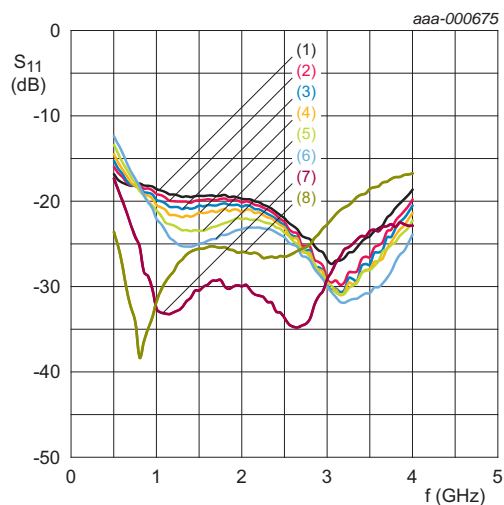
Fig 15. Input return loss as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; maximum current setting;
minimum attenuation.

- (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = +85\text{ }^{\circ}\text{C}$

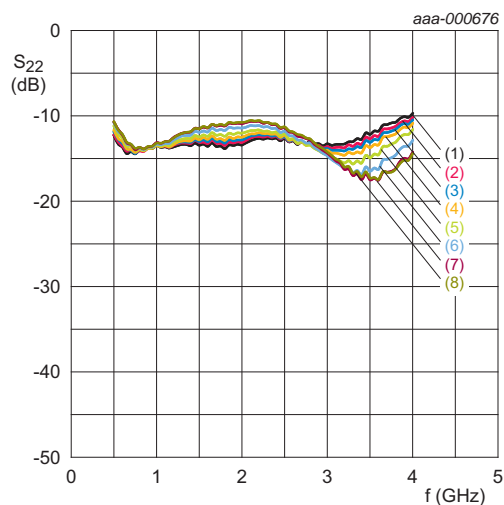
Fig 16. Output return loss as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; maximum current setting.

- (1) attenuation = 0x00 (minimum)
- (2) attenuation = 0x01
- (3) attenuation = 0x02
- (4) attenuation = 0x04
- (5) attenuation = 0x08
- (6) attenuation = 0x10
- (7) attenuation = 0x20
- (8) attenuation = 0x3F (maximum)

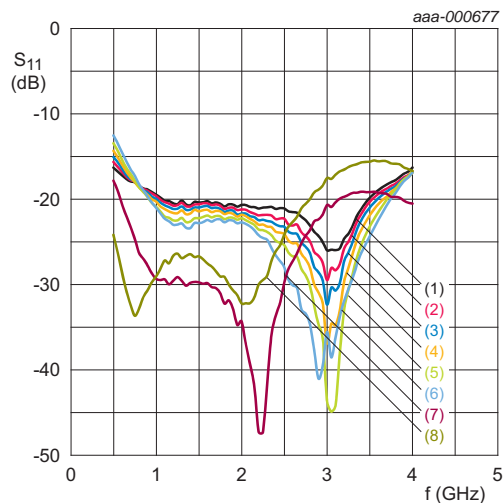
Fig 17. Input return loss as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; maximum current setting.

- (1) attenuation = 0x00 (minimum)
- (2) attenuation = 0x01
- (3) attenuation = 0x02
- (4) attenuation = 0x04
- (5) attenuation = 0x08
- (6) attenuation = 0x10
- (7) attenuation = 0x20
- (8) attenuation = 0x3F (maximum)

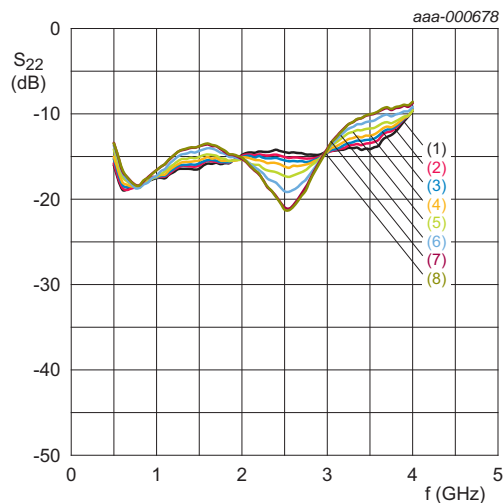
Fig 18. Output return loss as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; maximum current setting and shunt capacitor (C_{sh}).

- (1) attenuation = 0x00 (minimum)
- (2) attenuation = 0x01
- (3) attenuation = 0x02
- (4) attenuation = 0x04
- (5) attenuation = 0x08
- (6) attenuation = 0x10
- (7) attenuation = 0x20
- (8) attenuation = 0x3F (maximum)

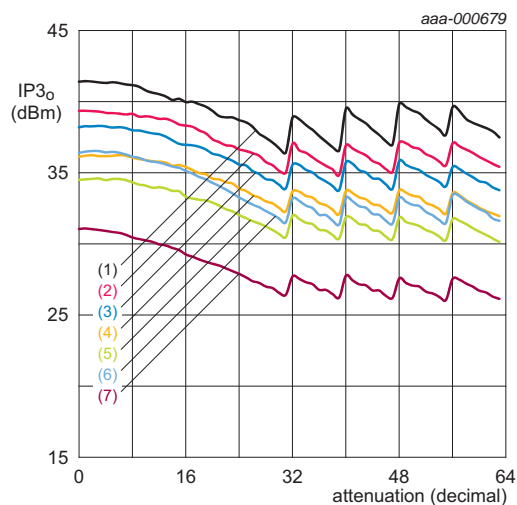
Fig 19. Input return loss with shunt capacitor as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; maximum current setting and shunt capacitor (C_{sh}).

- (1) attenuation = 0x00 (minimum)
- (2) attenuation = 0x01
- (3) attenuation = 0x02
- (4) attenuation = 0x04
- (5) attenuation = 0x08
- (6) attenuation = 0x10
- (7) attenuation = 0x20
- (8) attenuation = 0x3F (maximum)

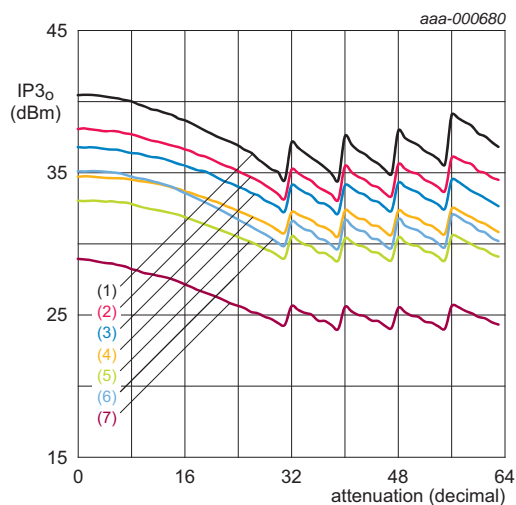
Fig 20. Output return loss with shunt capacitor as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = -40\text{ °C}$; maximum current setting.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

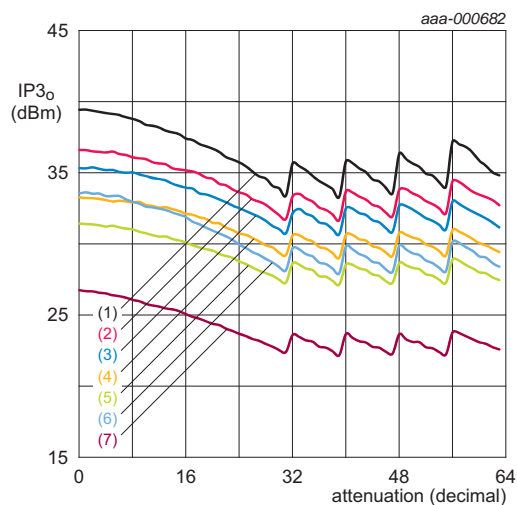
Fig 21. Output third-order intercept point as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; maximum current setting.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

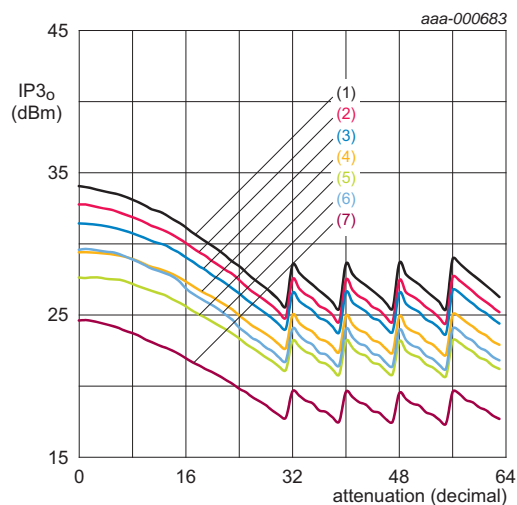
Fig 22. Output third-order intercept point as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 85\text{ °C}$; maximum current setting.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

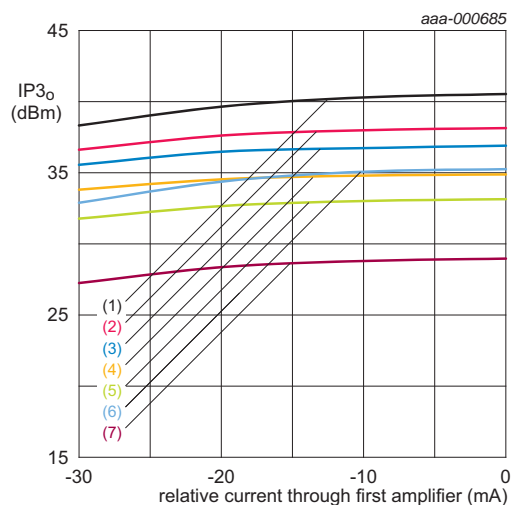
Fig 23. Output third-order intercept point as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; minimal current setting.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

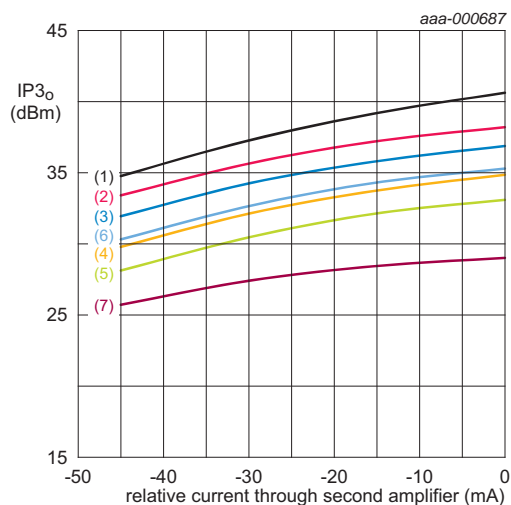
Fig 24. Output third-order intercept point as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; maximum gain;
maximum current through second amplifier.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

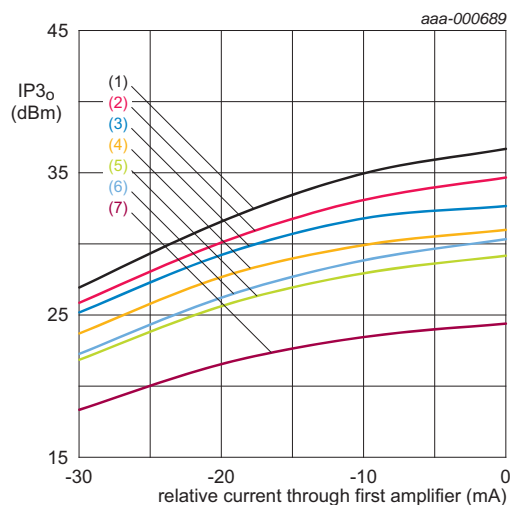
Fig 25. Output third-order intercept point as a function of relative current through first amplifier; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; maximum gain;
maximum current through first amplifier.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

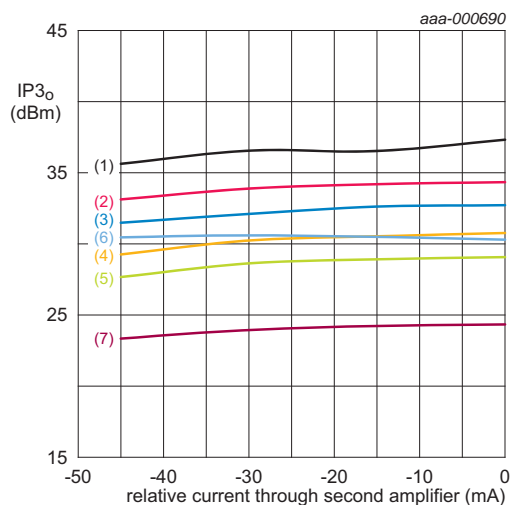
Fig 26. Output third-order intercept point as a function of relative current through second amplifier; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; minimum gain;
maximum current through second amplifier.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

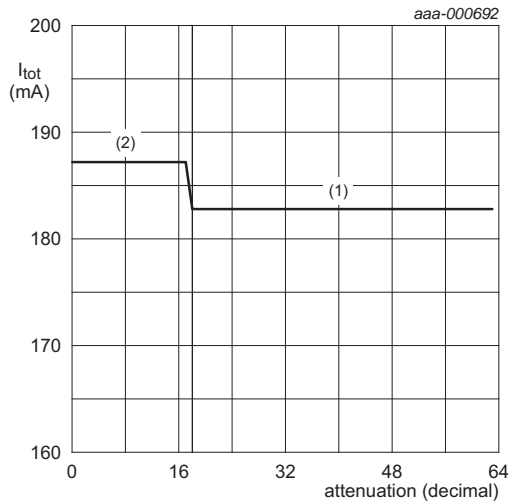
Fig 27. Output third-order intercept point as a function of relative current through first amplifier; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ °C}$; minimum gain;
maximum current through first amplifier.

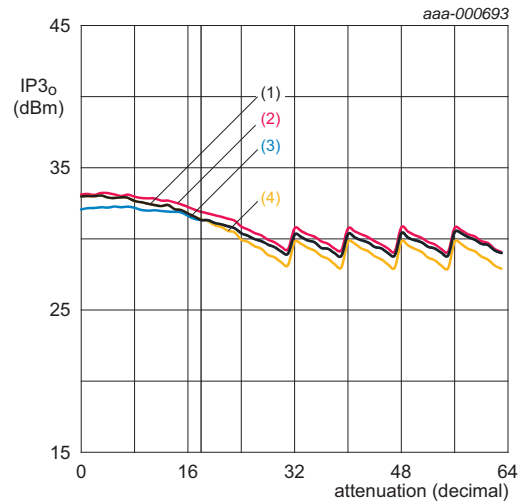
- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

Fig 28. Output third-order intercept point as a function of relative current through second amplifier; typical values



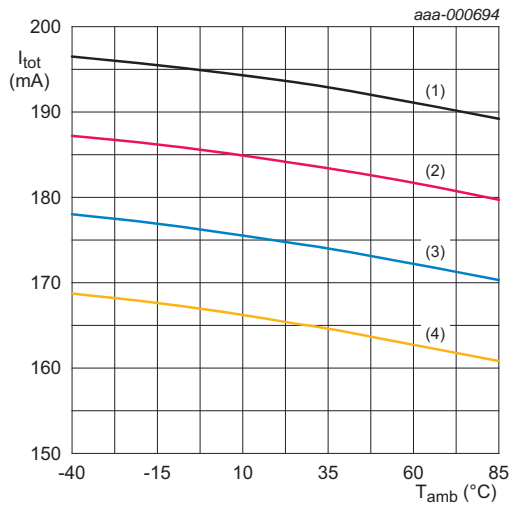
- $V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (1) $\Delta I_{AMP1} / \Delta I_{AMP2} = 0\text{ mA} / -15\text{ mA}$
 - (2) $\Delta I_{AMP1} / \Delta I_{AMP2} = -10\text{ mA} / 0\text{ mA}$

Fig 29. Total current as a function of attenuation state optimized for IP_{3O} ; typical values



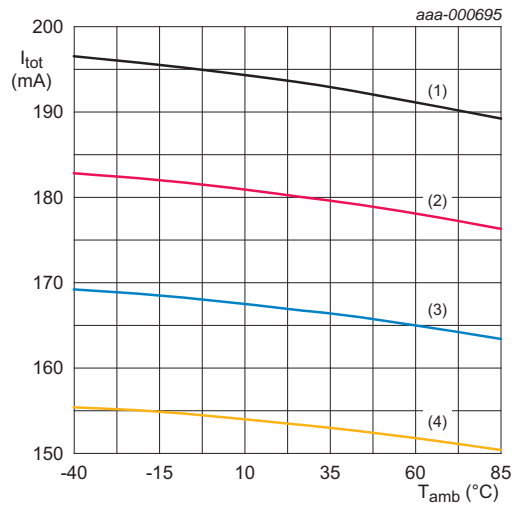
- $V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $f = 2.8\text{ GHz}$.
- (1) $\Delta I_{AMP1} / \Delta I_{AMP2} = I_{opt}$
 - (2) $\Delta I_{AMP1} / \Delta I_{AMP2} = 0\text{ mA} / 0\text{ mA}$
 - (3) $\Delta I_{AMP1} / \Delta I_{AMP2} = 0\text{ mA} / -15\text{ mA}$
 - (4) $\Delta I_{AMP1} / \Delta I_{AMP2} = -10\text{ mA} / 0\text{ mA}$

Fig 30. Output third-order intercept point as a function of attenuation state; typical values



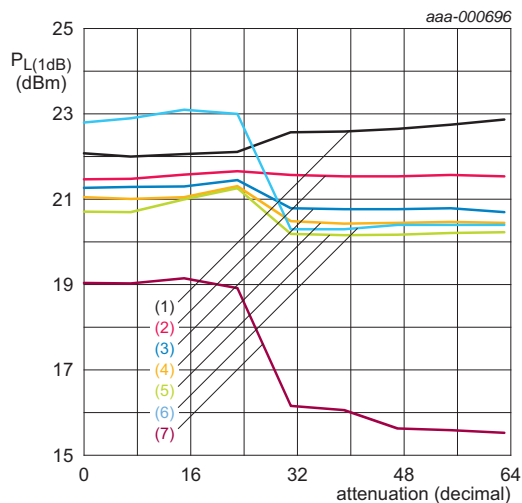
- $V_{SUP} = 5\text{ V}$; maximum current through second amplifier.
- (1) $I_{AMP1} = 0\text{ mA}$
 - (2) $I_{AMP1} = -10\text{ mA}$
 - (3) $I_{AMP1} = -20\text{ mA}$
 - (4) $I_{AMP1} = -30\text{ mA}$

Fig 31. Total current as a function of ambient temperature; typical values



- $V_{SUP} = 5\text{ V}$; maximum current through first amplifier.
- (1) $I_{AMP2} = 0\text{ mA}$
 - (2) $I_{AMP2} = -10\text{ mA}$
 - (3) $I_{AMP2} = -20\text{ mA}$
 - (4) $I_{AMP2} = -30\text{ mA}$

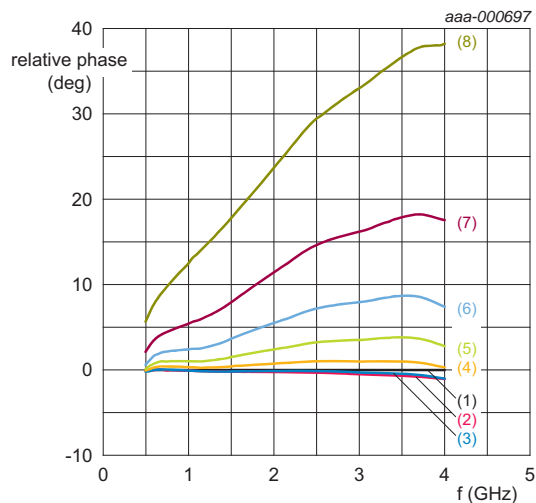
Fig 32. Total current as a function of ambient temperature; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 85\text{ }^{\circ}\text{C}$; maximum current setting; attenuation states 0, 7, 15, 23, 31, 39, 47, 55 and 63 are depicted.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

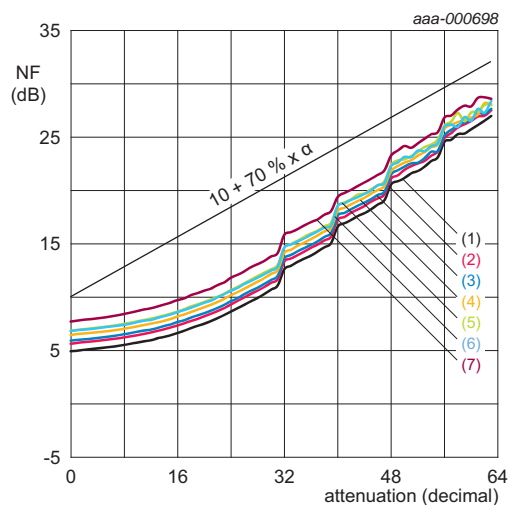
Fig 33. Output power at 1 dB gain compression as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; maximum current setting.

- (1) attenuation = 0x00 (minimum)
- (2) attenuation = 0x01
- (3) attenuation = 0x02
- (4) attenuation = 0x04
- (5) attenuation = 0x08
- (6) attenuation = 0x10
- (7) attenuation = 0x20
- (8) attenuation = 0x3F (maximum)

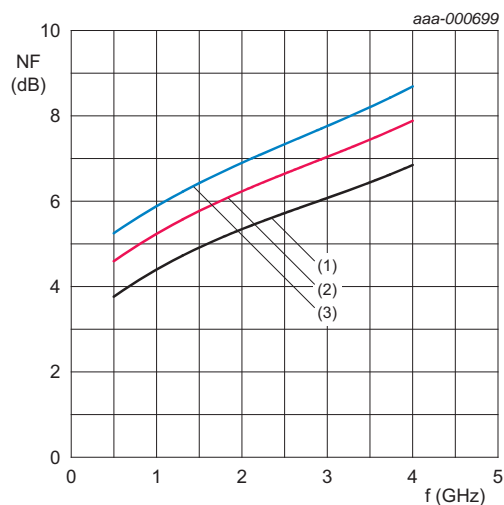
Fig 34. Relative phase as a function of frequency; typical values



$V_{SUP} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; maximum current setting.

- (1) $f = 0.7\text{ GHz}$
- (2) $f = 1.4\text{ GHz}$
- (3) $f = 1.7\text{ GHz}$
- (4) $f = 2.2\text{ GHz}$
- (5) $f = 2.8\text{ GHz}$
- (6) $f = 2.8\text{ GHz}$ and C_{sh} used
- (7) $f = 3.8\text{ GHz}$

Fig 35. Noise figure as a function of attenuation state; typical values



$V_{SUP} = 5\text{ V}$; maximum gain and maximum current setting.

- (1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
- (2) $T_{amb} = +25\text{ }^{\circ}\text{C}$
- (3) $T_{amb} = +85\text{ }^{\circ}\text{C}$

Fig 36. Noise figure as a function of frequency; typical values

12. Package outline

HVQFN32: plastic thermal enhanced very thin quad flat package; no leads;
32 terminals; body 5 x 5 x 0.85 mm

SOT617-3

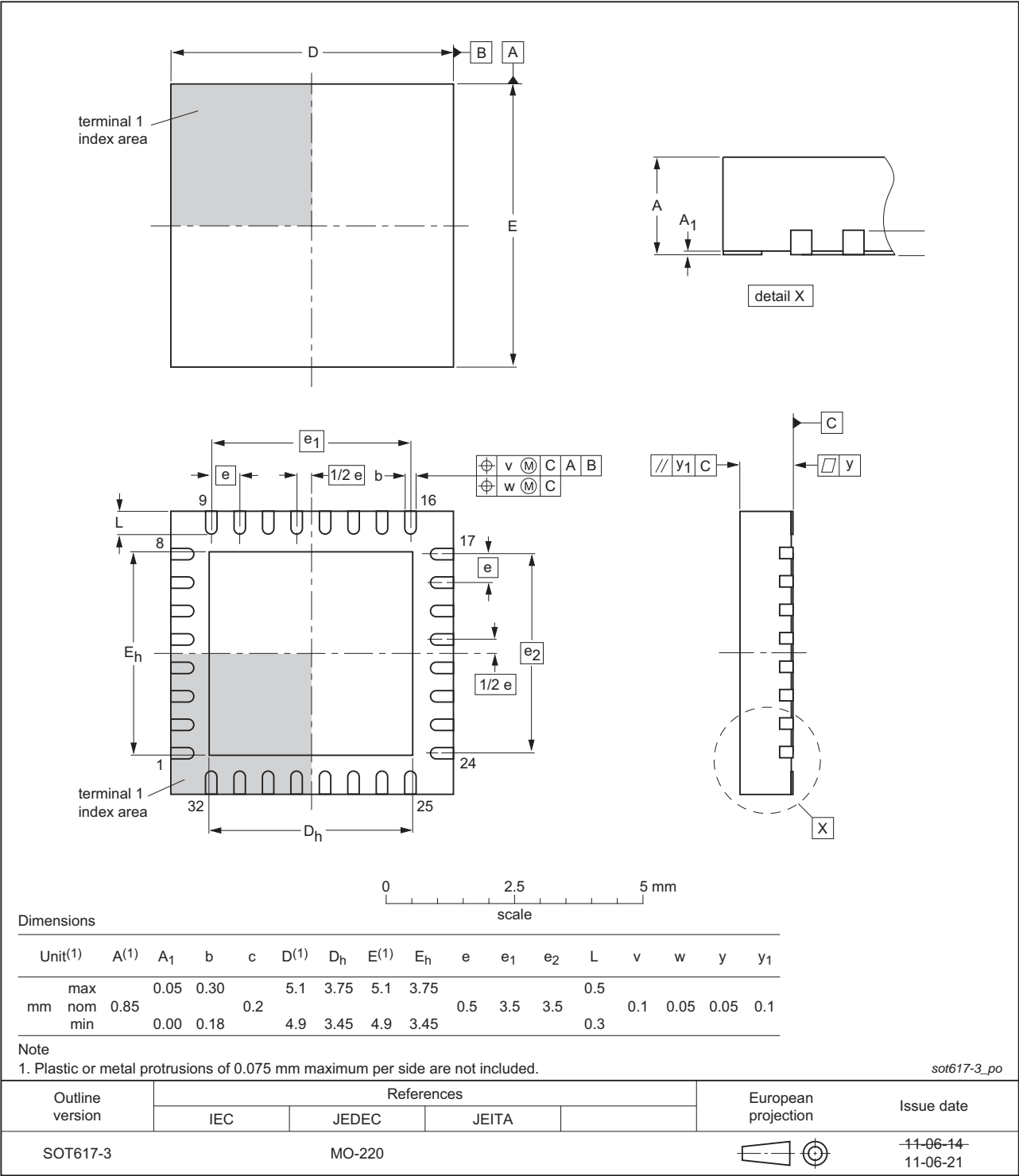


Fig 37. Package outline SOT617-3 (HVQFN32)

13. Packing information

The BGA7210 will be delivered in reel pack SMD 7", 1500 pieces per reel.

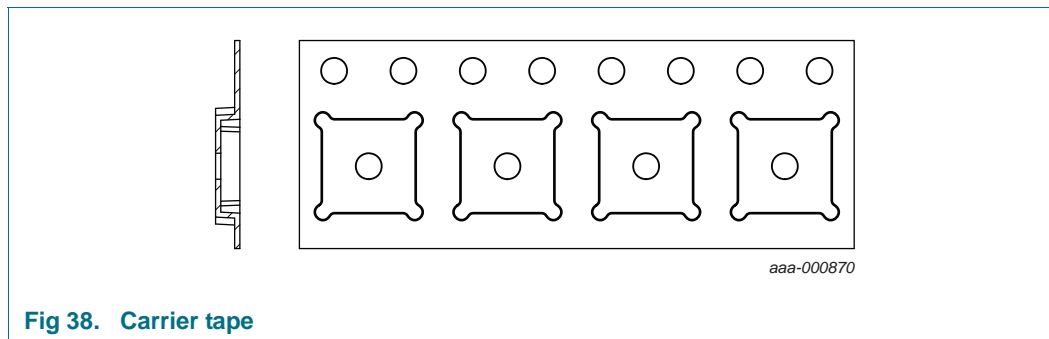


Fig 38. Carrier tape

14. Abbreviations

Table 15. Abbreviations

Acronym	Description
CDM	Charged Device Model
ESD	ElectroStatic Discharge
DSA	Digital Step Attenuator
HBM	Human Body Model
IF	Intermediate Frequency
MMIC	Monolithic Microwave Integrated Circuit
POR	Power-On Reset
RF	Radio Frequency
SPI	Serial Peripheral Interface
USB	Universal Serial Bus
WiMAX	Worldwide Interoperability for Microwave Access

15. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGA7210 v.5	20170120	Product data sheet	-	BGA7210 v.4
Modifications:	<ul style="list-style-type: none"> • Section 1: added BTS6001A according to our new naming convention 			
BGA7210 v.4	20130128	Product data sheet	-	BGA7210 v.3
Modifications:	<ul style="list-style-type: none"> • Table 4: updated. 			
BGA7210 v.3	20121224	Product data sheet	-	BGA7210 v.2
BGA7210 v.2	20120104	Product data sheet	-	BGA7210 v.1
BGA7210 v.1	20111213	Preliminary data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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17. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

18. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	2
2	Pinning information	3
2.1	Pinning	3
2.2	Pin description	3
3	Ordering information	4
4	Marking	4
5	Limiting values	4
6	Thermal characteristics	5
7	Static characteristics	5
8	Dynamic characteristics	6
9	Serial Peripheral Interface	8
9.1	Command word format	8
9.2	Setting current and attenuation	8
9.3	SPI timing	10
10	Power-up and power save	10
11	Application information	11
11.1	Application board	11
11.2	Characteristics	13
12	Package outline	26
13	Packing information	27
14	Abbreviations	27
15	Revision history	27
16	Legal information	28
16.1	Data sheet status	28
16.2	Definitions	28
16.3	Disclaimers	28
16.4	Trademarks	29
17	Contact information	29
18	Contents	30

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